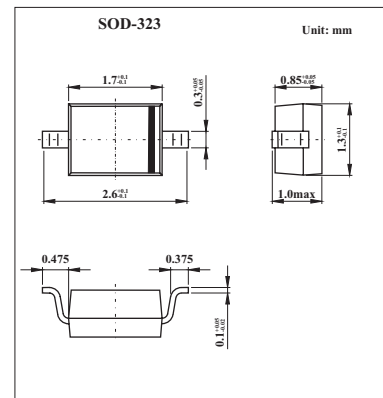


BAP51-03

■ Features

- Low diode capacitance
- Low diode forward resistance.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Min | Max | Unit |
|---|---------------|-----|------|------|
| continuous reverse voltage | V_R | | 50 | V |
| continuous forward current | I_F | | 50 | mA |
| total power dissipation $T_s = 90^\circ\text{C}$ | P_{tot} | | 500 | mW |
| storage temperature | T_{stg} | -65 | +150 | °C |
| junction temperature | T_j | -65 | +150 | °C |
| thermal resistance from junction to soldering point | $R_{th\ j-s}$ | | 120 | K/W |

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--------------------------|----------|---|-----|------|------|----------|
| forward voltage | V_F | $I_F = 50\text{ mA}$ | | 0.95 | 1.1 | V |
| reverse voltage | V_R | $I_R = 10\ \mu\text{A}$ | 50 | | | V |
| reverse current | I_R | $V_R = 50\text{ V}$ | | | 100 | nA |
| diode capacitance | C_d | $V_R = 0; f = 1\text{ MHz}$ | | 0.4 | | pF |
| | | $V_R = 1\text{ V}; f = 1\text{ MHz}$ | | 0.3 | 0.55 | |
| | | $V_R = 5\text{ V}; f = 1\text{ MHz}$ | | 0.2 | 0.35 | |
| diode forward resistance | r_D | $I_F = 0.5\text{ mA}; f = 100\text{ MHz}; \text{note 1}$ | | 5.5 | 40 | Ω |
| | | $I_F = 1\text{ mA}; f = 100\text{ MHz}; \text{note 1}$ | | 3.6 | 25 | |
| | | $I_F = 10\text{ mA}; f = 100\text{ MHz}; \text{note 1}$ | | 1.5 | 5 | |
| charge carrier life time | τ_L | when switched from $I_F = 10\text{ mA}$ to $I_R = 6\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 3\text{ mA}$ | | 550 | | ns |

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

■ Marking

| | |
|---------|----|
| Marking | A5 |
|---------|----|